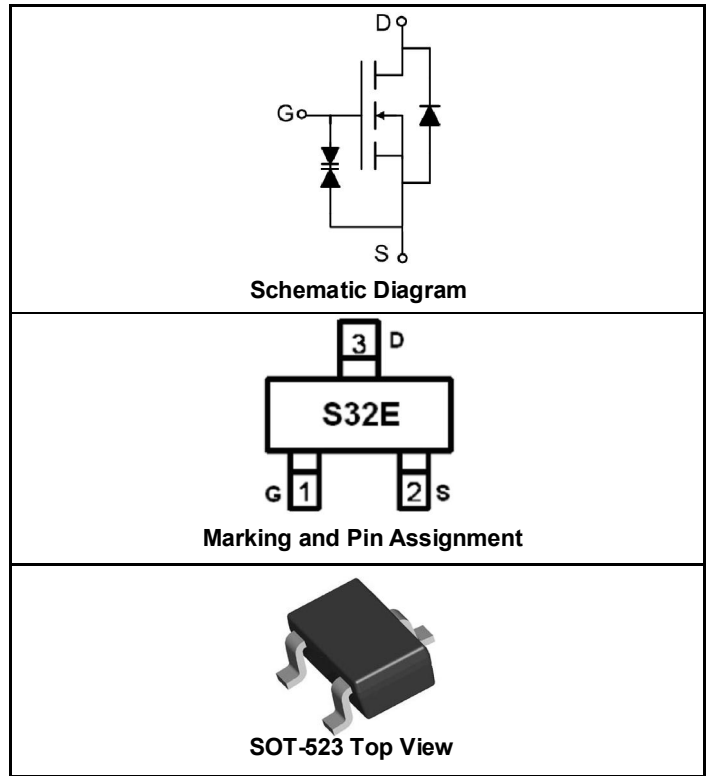


GENERAL FEATURES

- $V_{DS} = 30V, I_D = 0.1A$
- $R_{DS(ON)} < 8\Omega @ V_{GS}=4V$
- $R_{DS(ON)} < 13\Omega @ V_{GS}=2.5V$
- ESD Rating: 1000V HBM
- High Power and current handing capability
- Lead free product
- Surface Mount Package

APPLICATIONS

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays



PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape Width	Quantity
S32E	SSF32E0E	SOT-523	Ø180mm	8 mm	3000 units

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	0.1	A
	$I_D(70^\circ\text{C})$	0.07	
	I_{DM}	0.4	A
Maximum Power Dissipation	P_D	0.2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	400	$^\circ\text{C/W}$
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ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu\text{A}$	30			V

Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 5V, V_{DS}=0V$			100	nA
		$V_{GS}=\pm 10V, V_{DS}=0V$			150	nA
		$V_{GS}=\pm 20V, V_{DS}=0V$			10	μA
Gate-Source Breakdown Voltage	BV_{GSO}	$V_{DS}=0V, I_G=\pm 250\mu A$	± 20			V
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.8		1.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4V, I_D=0.01A$		5	8	Ω
		$V_{GS}=2.5V, I_D=0.001A$		7	13	
Forward Transconductance	g_{FS}	$V_{DS}=3V, I_D=0.01A$	0.02			S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=5V, V_{GS}=0V,$ $F=1.0MHz$		45		PF
Output Capacitance	C_{oss}			12		PF
Reverse Transfer Capacitance	C_{rss}			7		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=5V, V_{GS}=5V,$ $R_{GEN}=10\Omega, R_L=500\Omega$ $I_D=0.01A$		15		nS
Turn-Off Delay Time	$t_{d(off)}$			75		nS
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=0.01A$			1.3	V

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

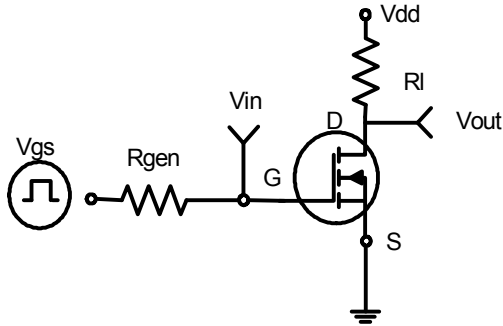


Figure 1: Switching Test Circuit

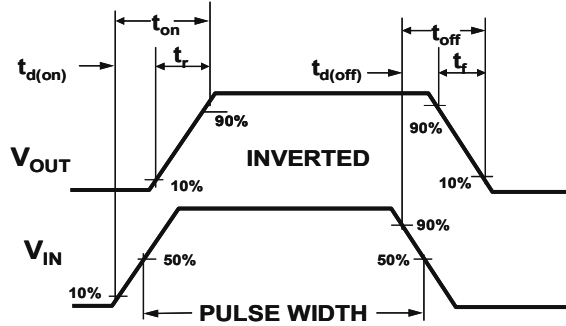


Figure 2: Switching Waveforms

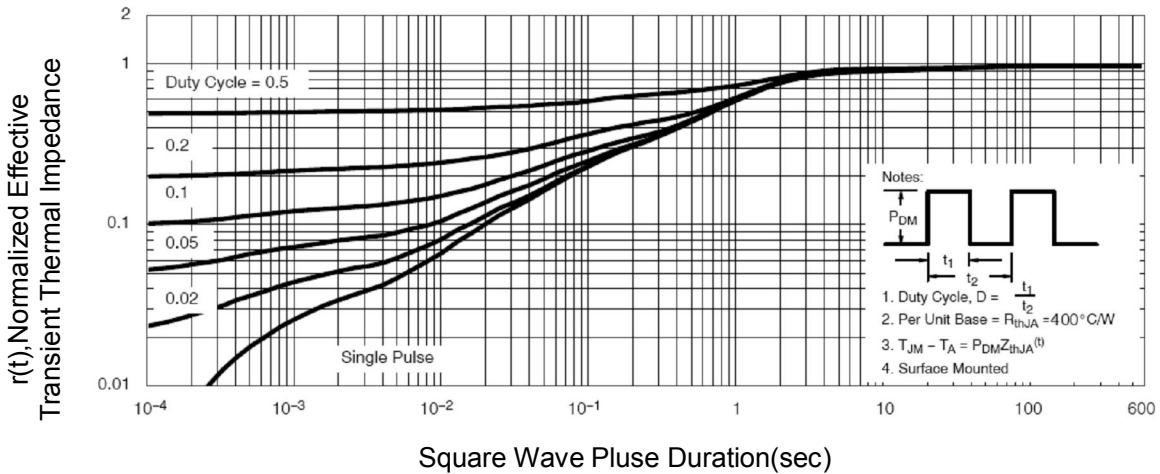
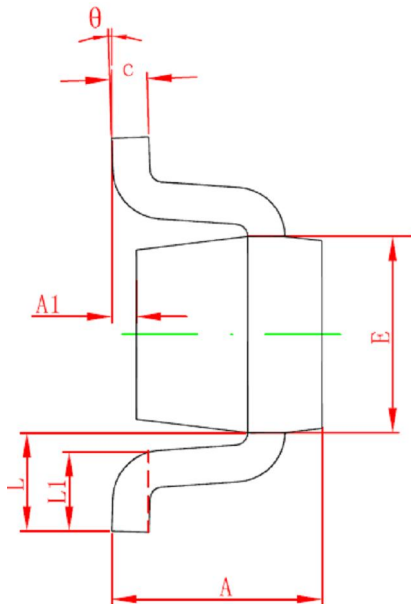
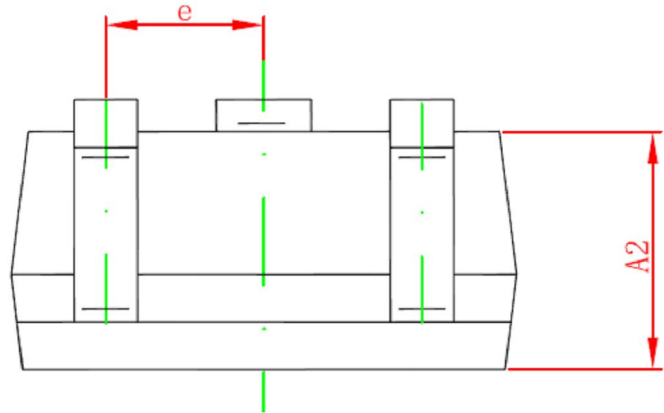
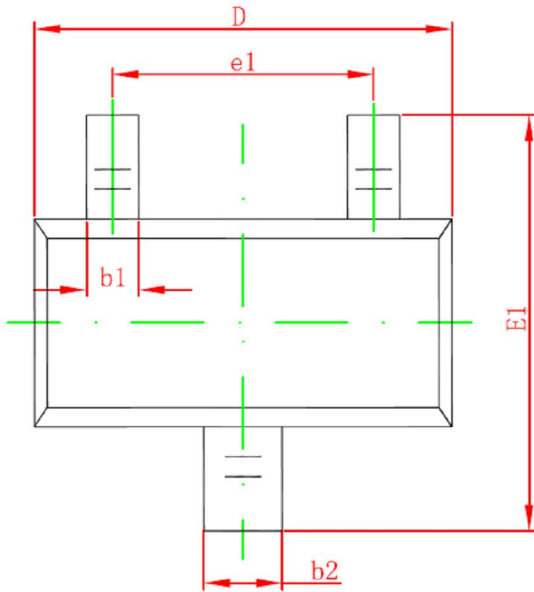


Figure 3 Normalized Maximum Transient Thermal Impedance

SOT-523 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT: mm)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
c	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500TYP	
e1	0.900	1.100
L	0.400REF	
L1	0.260	0.460
θ	0°	8°

NOTES

- All dimensions are in millimeters.
- Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
- Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- Dimension L is measured in gauge plane.
- Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.